

# ROM MEMORY AND DECODERS

INEL4207

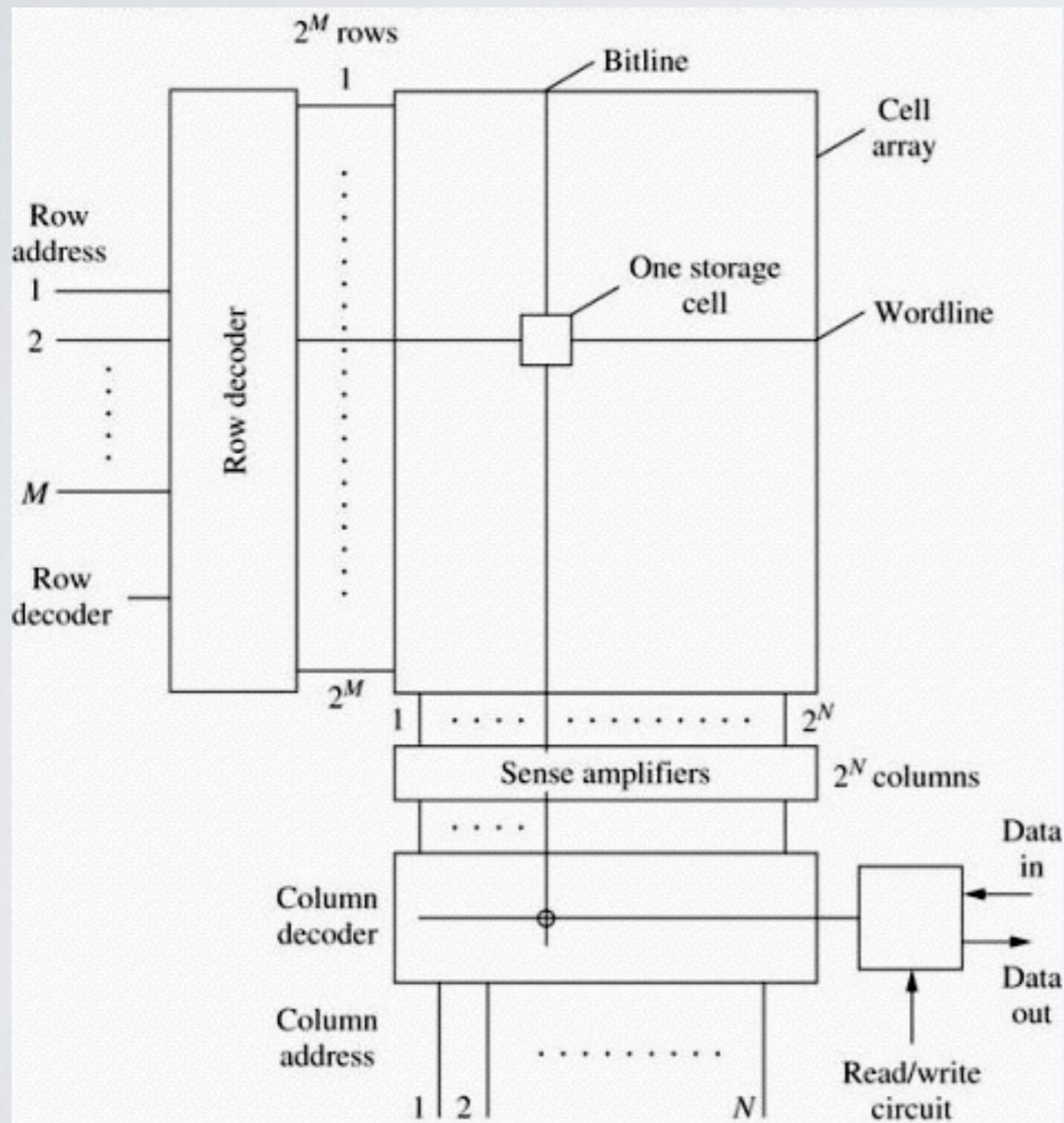
# RANDOM ACCESS MEMORY

- Random Access Memory (RAM)
  - read and write memory
  - volatile
- Static RAM (SRAM)
  - store information as long as power is applied
  - will not lose data during a read cycle
- Dynamic RAM (DRAM)
  - uses a capacitor to store data
  - must be refreshed periodically to prevent data loss
  - read cycles destroy DRAM data (must be re-written)
- SRAM takes  $\sim 4 \times$  DRAM Silicon area

# READ-ONLY MEMORY (ROM)

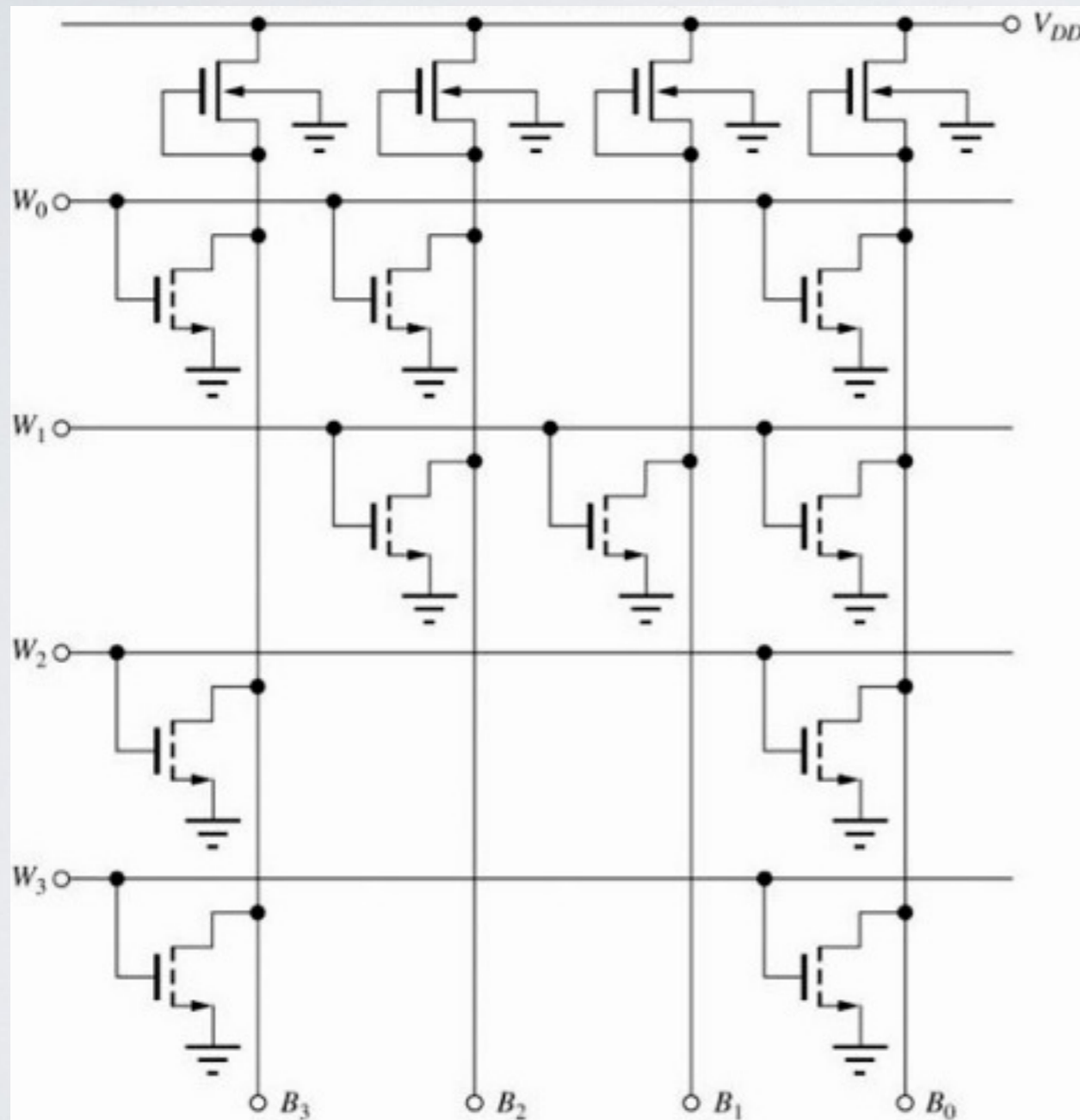
- Non-volatile
- ROM is often needed in digital systems such as:
  - Holding the instruction set for a microprocessor
  - Firmware
  - Calculator plug-in modules
  - Cartridge style video games

# A 256-MBYTE MEMORY CHIP



- Memory block contains  $2^{M+N}$  storage locations
- When a bit is selected,
  - sense amplifiers: used to read/write to the RAM location
- Horizontal rows: **wordlines**
- Vertical lines: **bitlines**

# READ-ONLY MEMORY (ROM)



- The basic structure of the NMOS static ROM is shown in the figure
- The existence of a NMOS means a “0” is stored at that address otherwise a “1” is stored
- The major downfall to this particular circuit is that it dissipates a lot of power

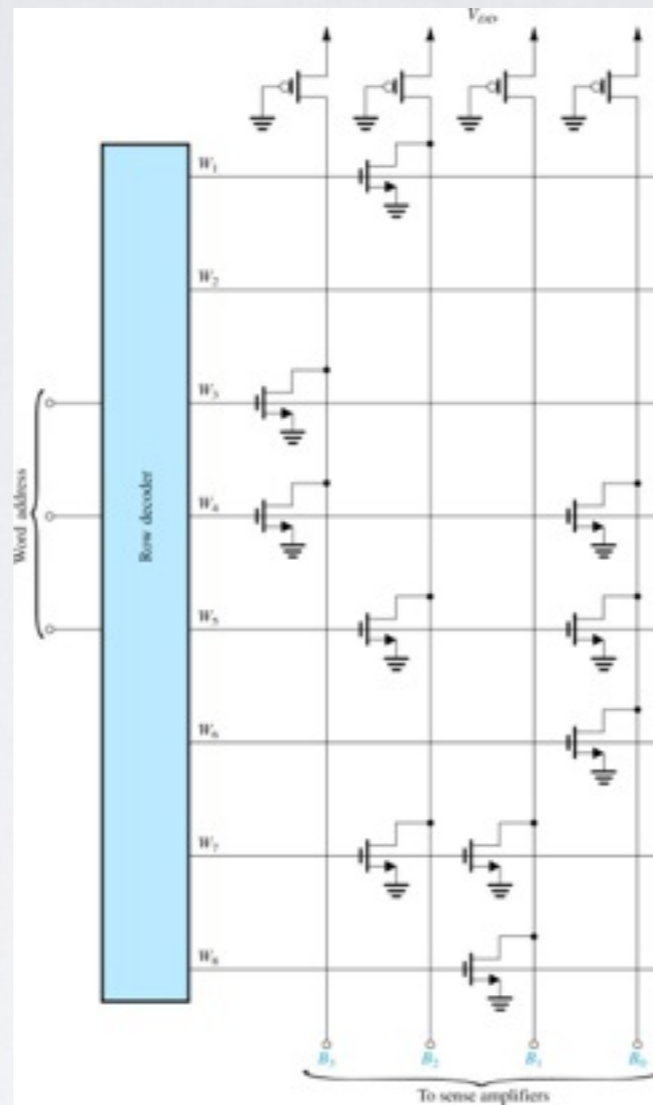
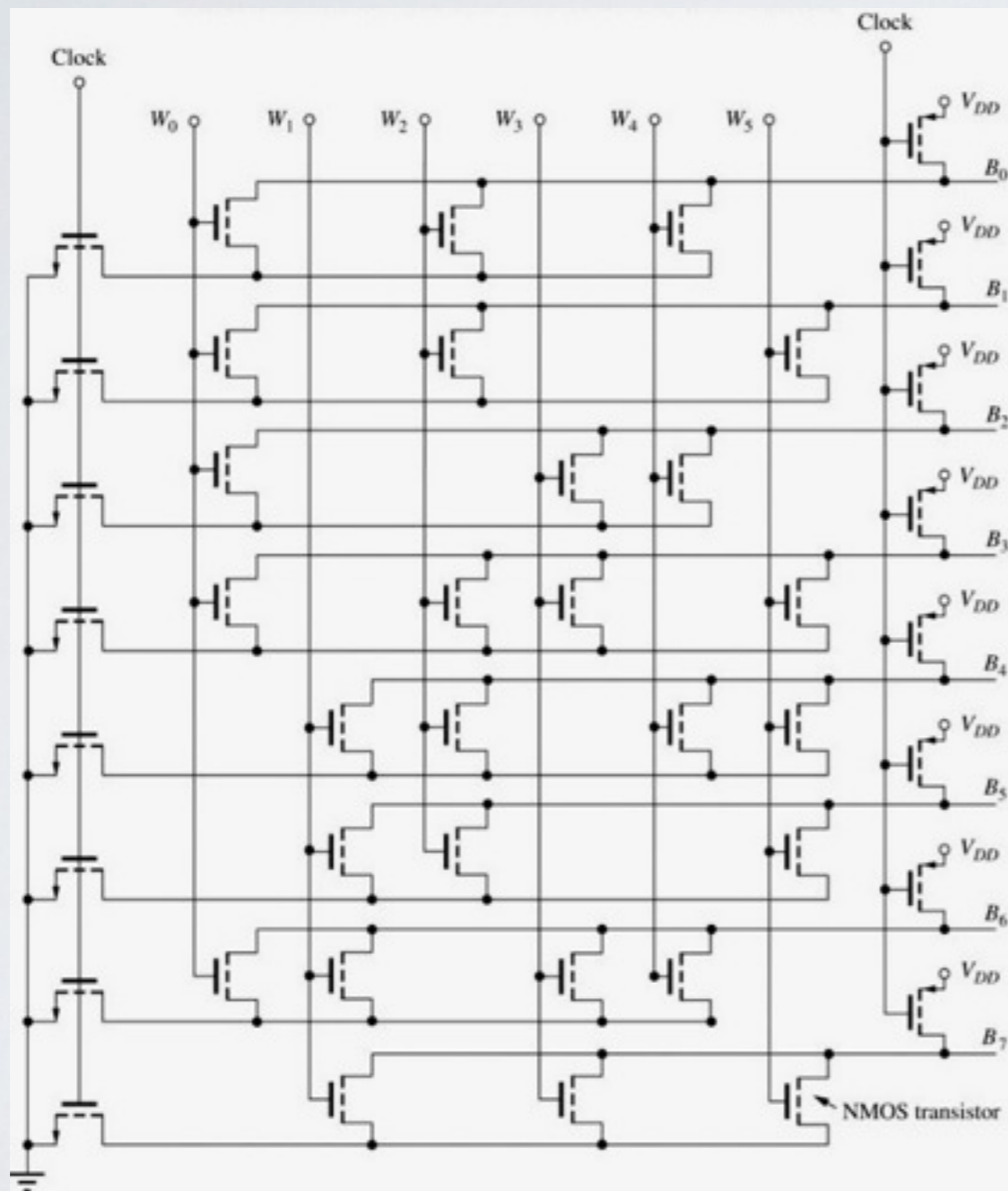


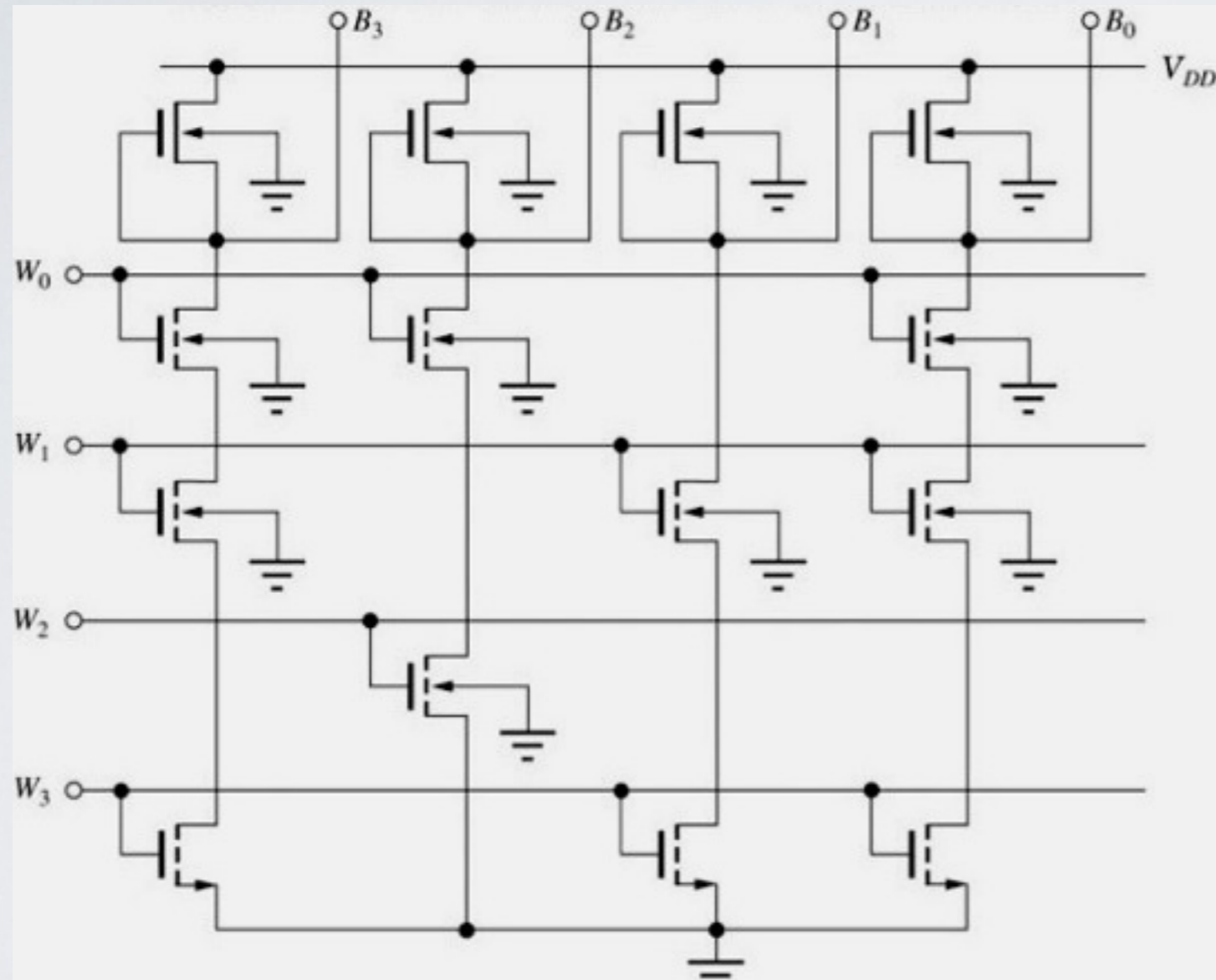
Figure 16.30 A simple MOS ROM organized as 8 words  $\times$  4 bits.

# READ-ONLY MEMORY (ROM)



- The domino CMOS ROM is one technique used to lower the amount of power dissipation

# NAND-ARRAY STRUCTURE ROM



- Can be directly used with NAND decoder
- Active-low word bits:
  - All  $W$ 's are HIGH except selected row
  - absence of FET makes bit low;
  - presence makes bit high



# NMOS NOR ADDRESS DECODERS

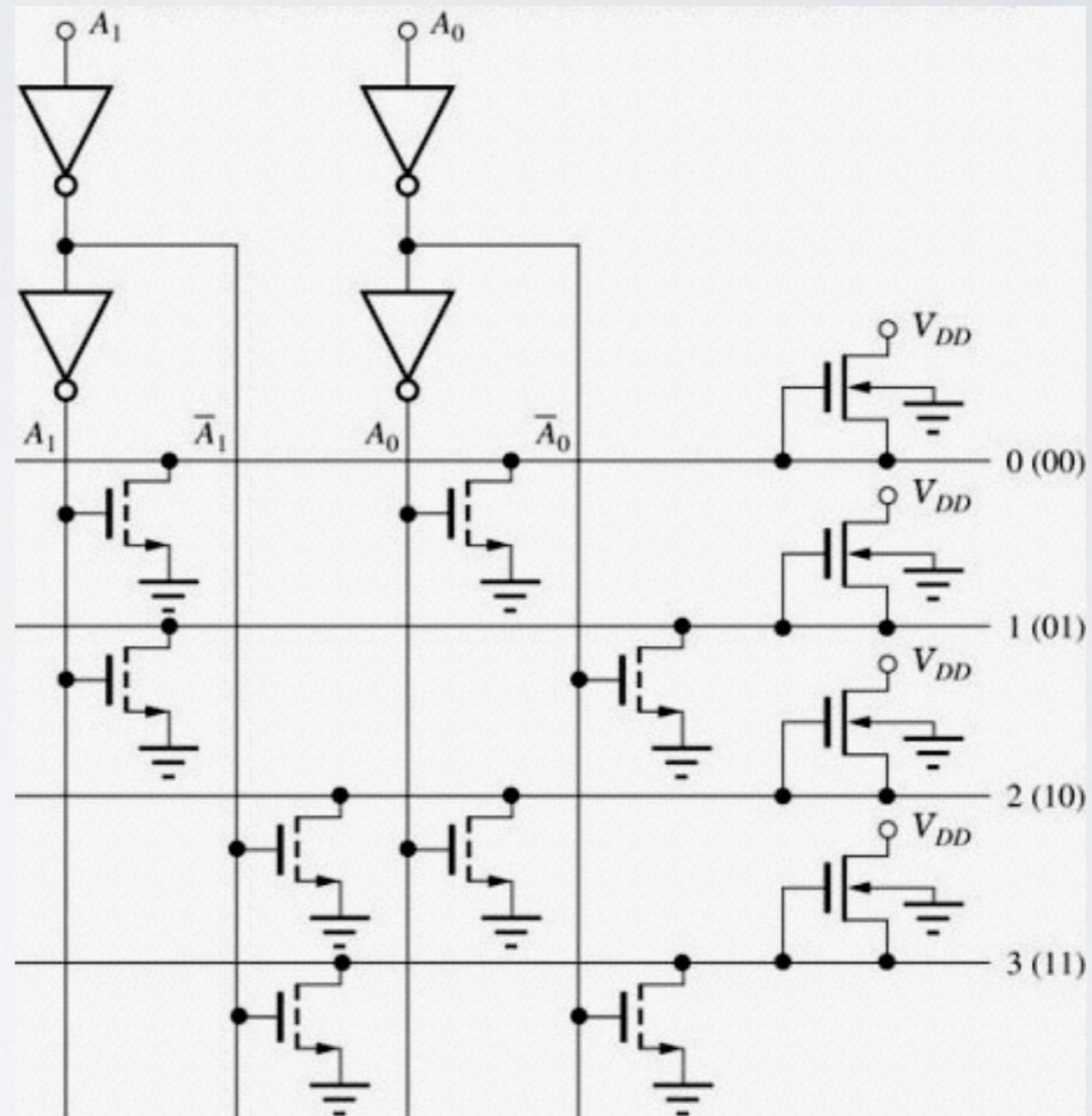
- Output 0 is high if both  $A_0$  and  $A_1$  are low

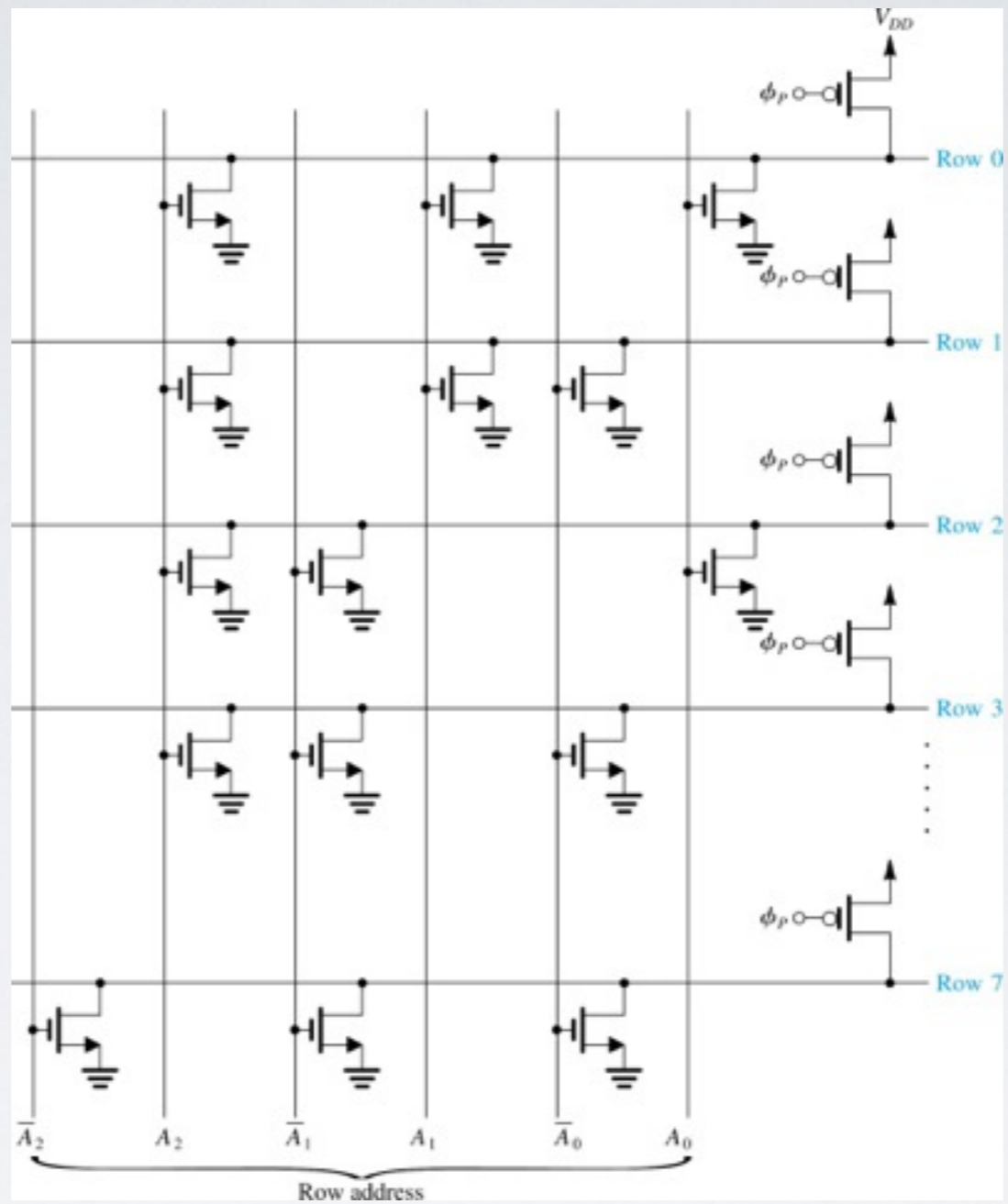
$$\text{Row 0} = (A_1 + A_0)'$$

$$\text{Row 1} = (A_1 + A_0')$$

$$\text{Row 2} = (A_1' + A_0)'$$

$$\text{Row 3} = (A_1' + A_0')$$





**Figure 16.25** A NOR address decoder in array form. One out of eight lines (row lines) is selected using a 3-bit address.

# NMOS NAND ADDRESS DECODERS

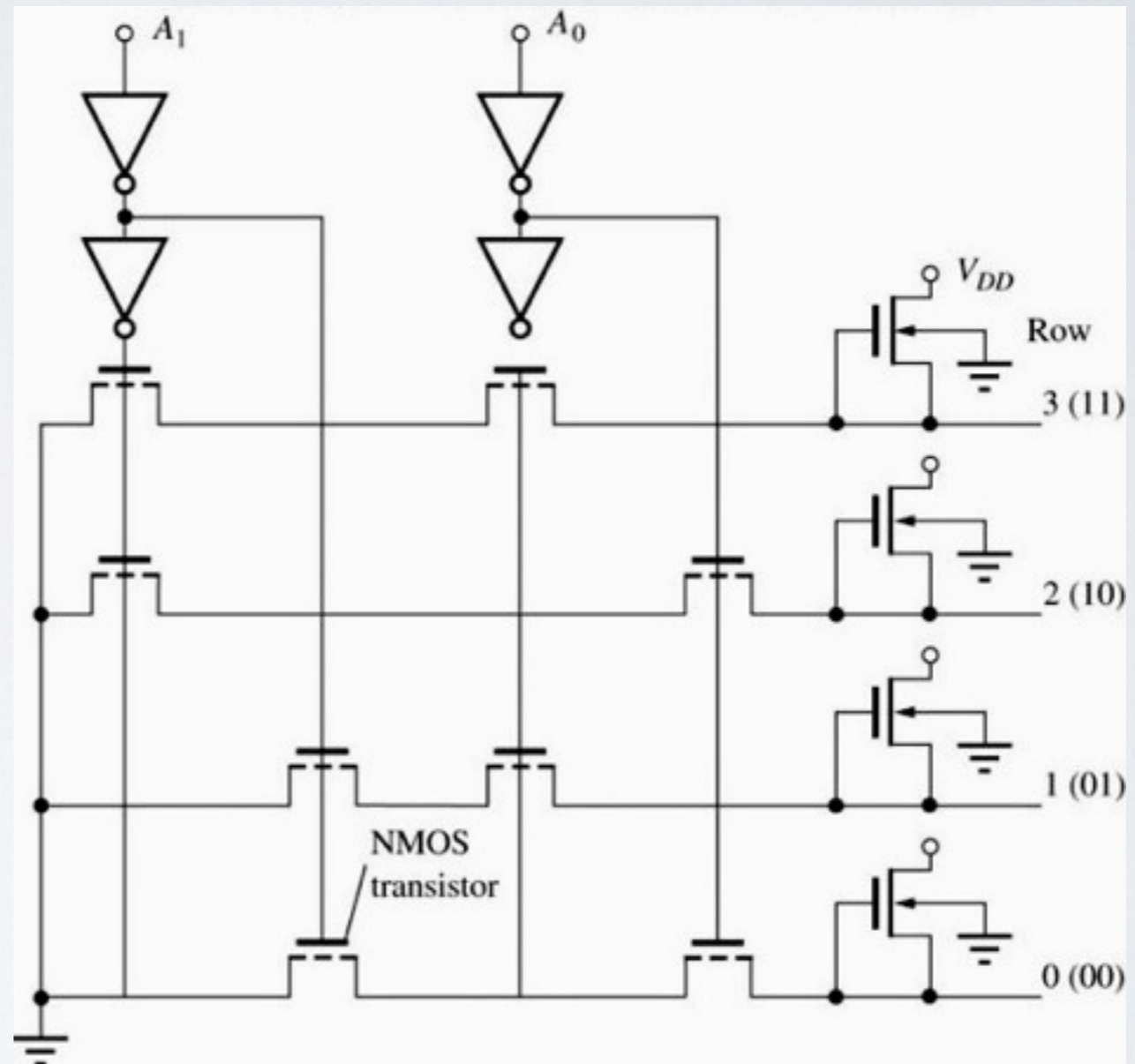
- Output 3 is low if both  $A_0$  and  $A_1$  are high

$$\text{Row 0} = (A_1' A_0')$$

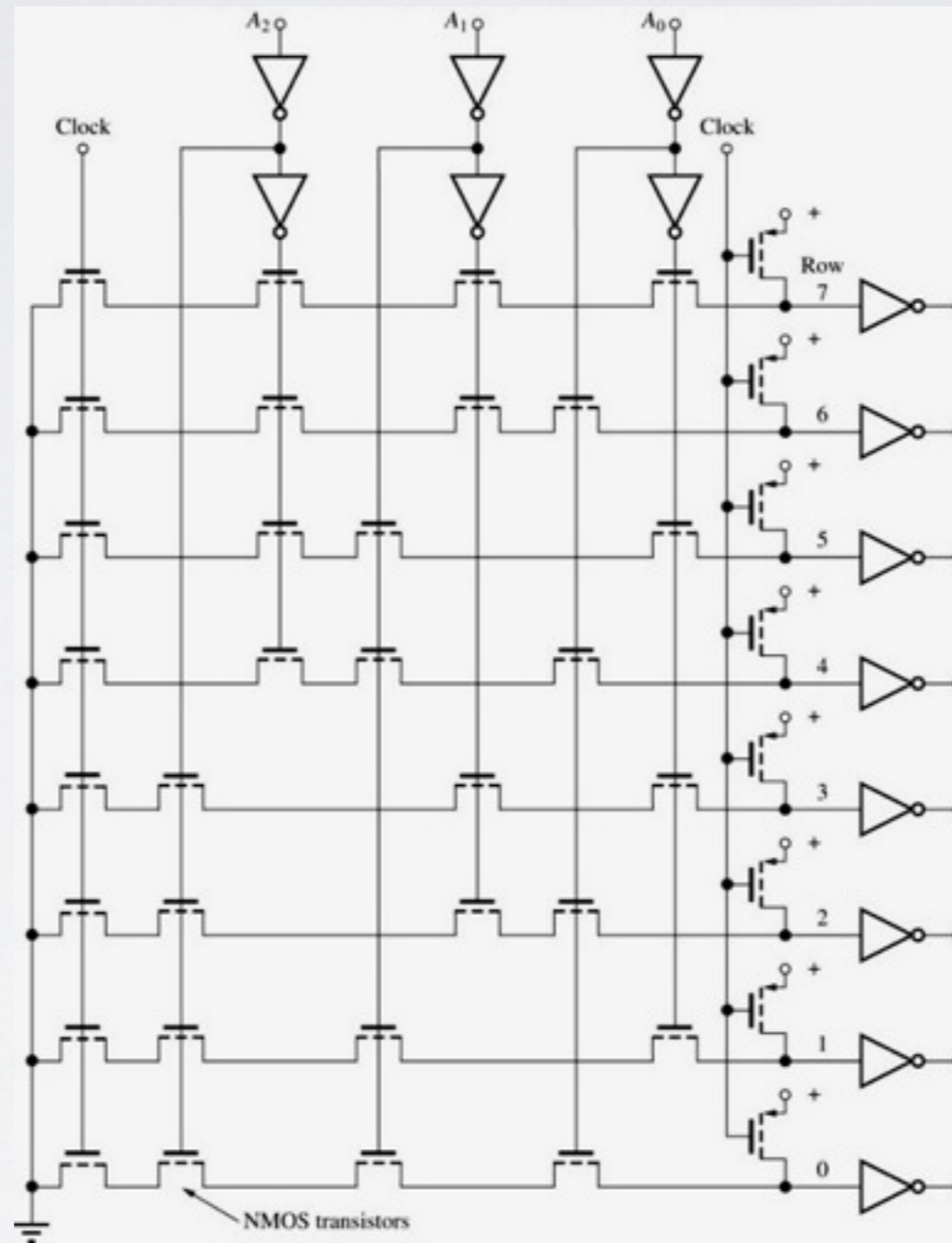
$$\text{Row 1} = (A_1' A_0)$$

$$\text{Row 2} = (A_1 \cdot A_0')$$

$$\text{Row 3} = (A_1 \cdot A_0)$$

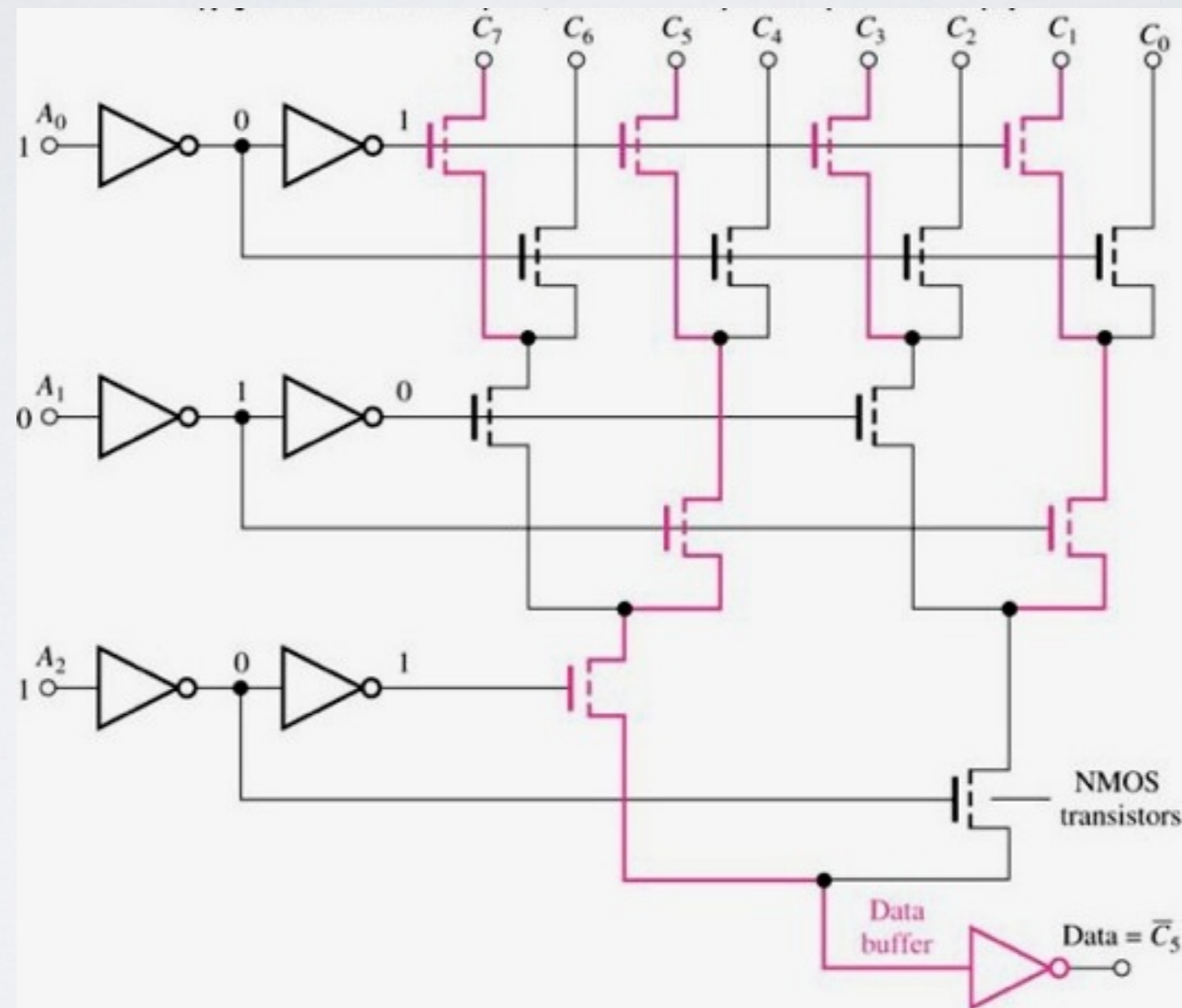


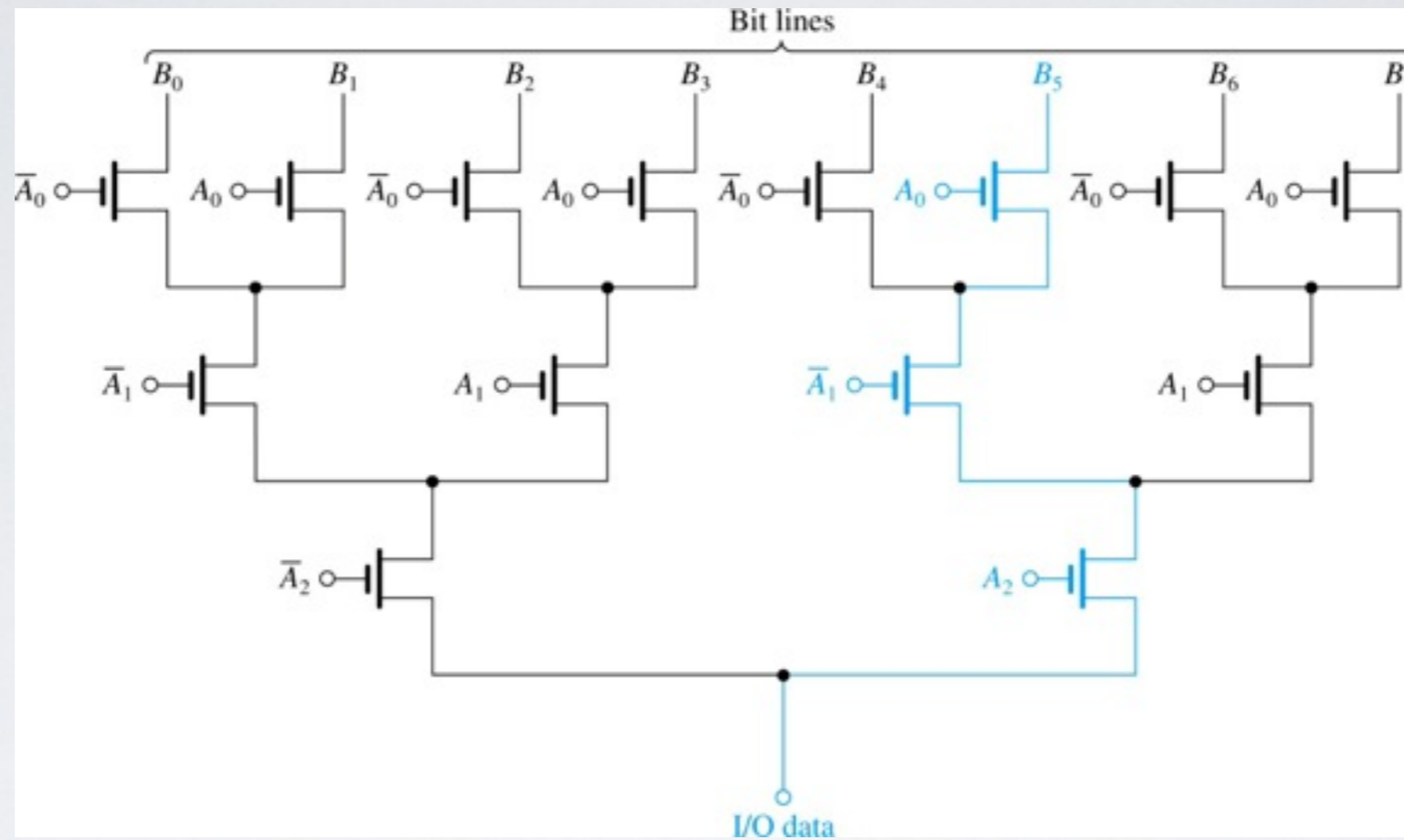
# DOMINO CMOS ADDRESS DECODERS



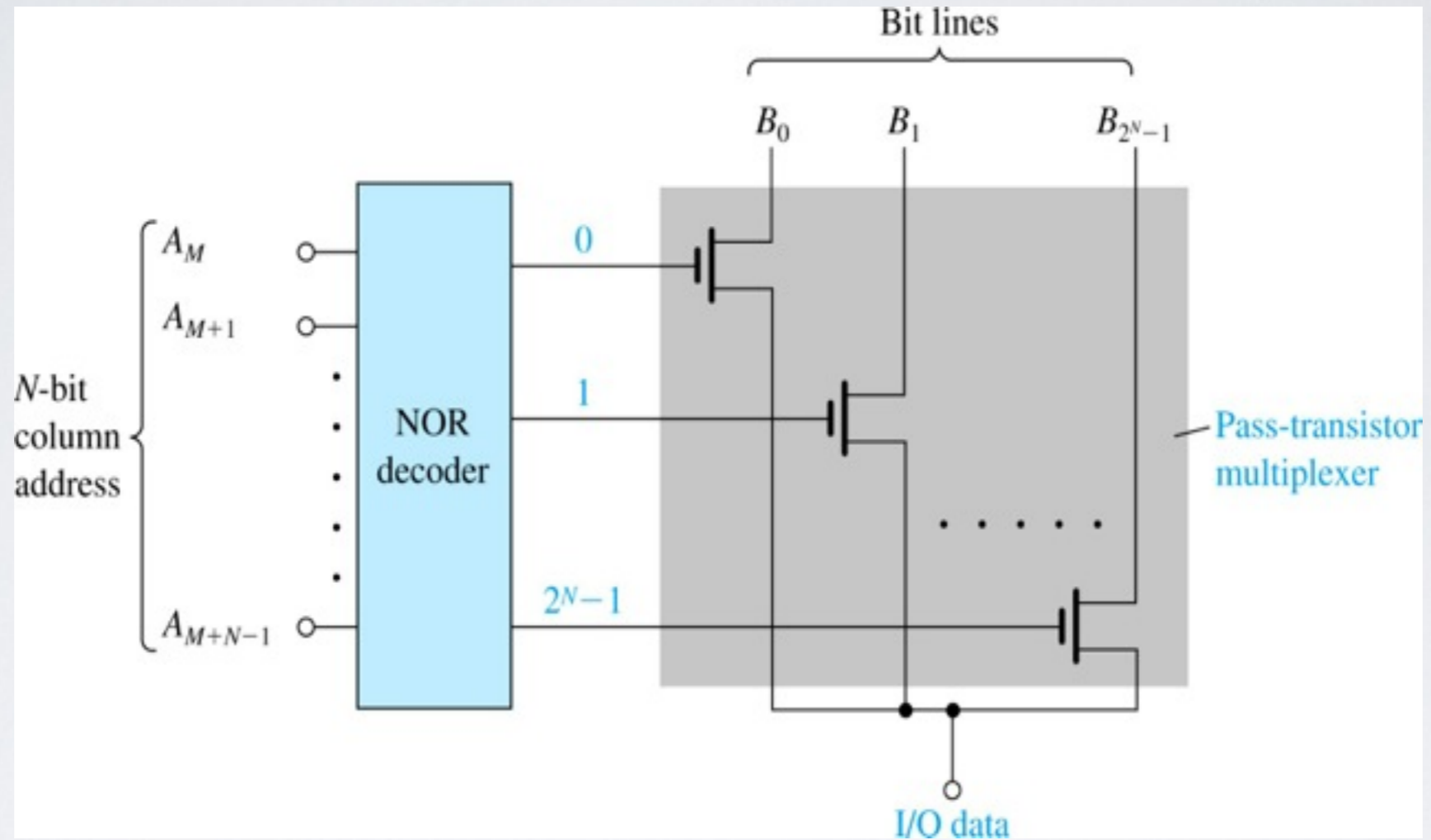
# PASS-TRANSISTOR COLUMN DECODER

- 3-bit column data selector using pass-transistor logic

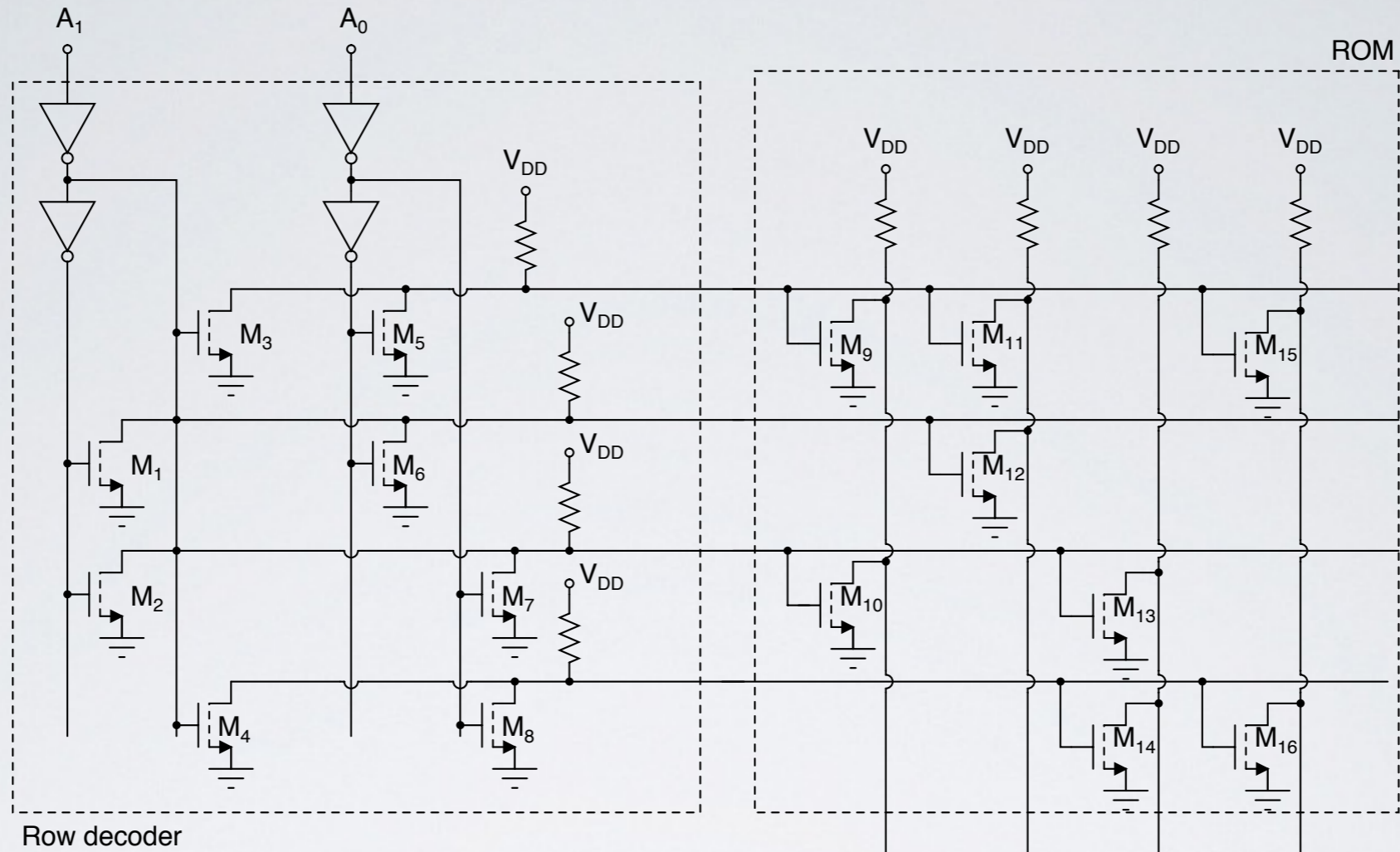




**Figure 16.27** A tree column decoder. Note that the colored path shows the transistors that are conducting when  $A_0 = 1$ ,  $A_1 = 0$ , and  $A_2 = 1$ , the address that results in connecting  $B_5$  to the data line.

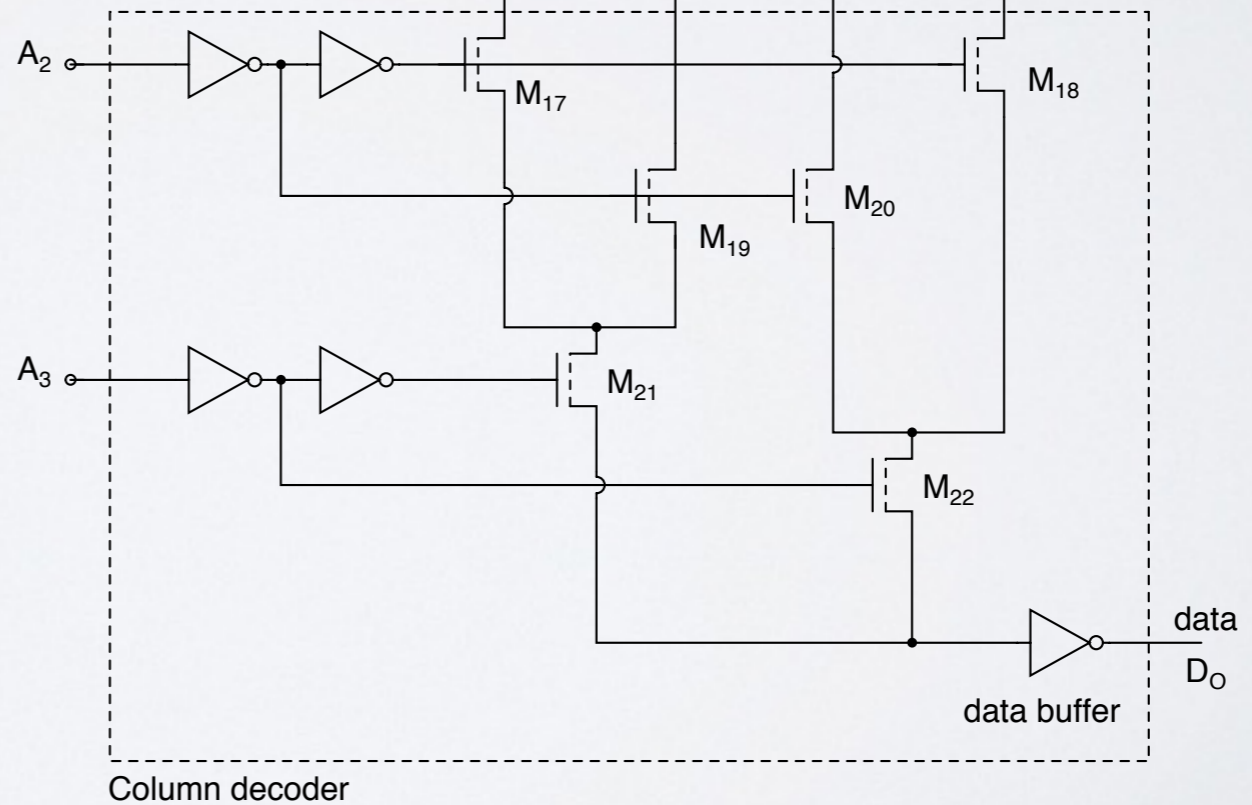


**Figure 16.26** A column decoder realized by a combination of a NOR decoder and a pass-transistor multiplexer.

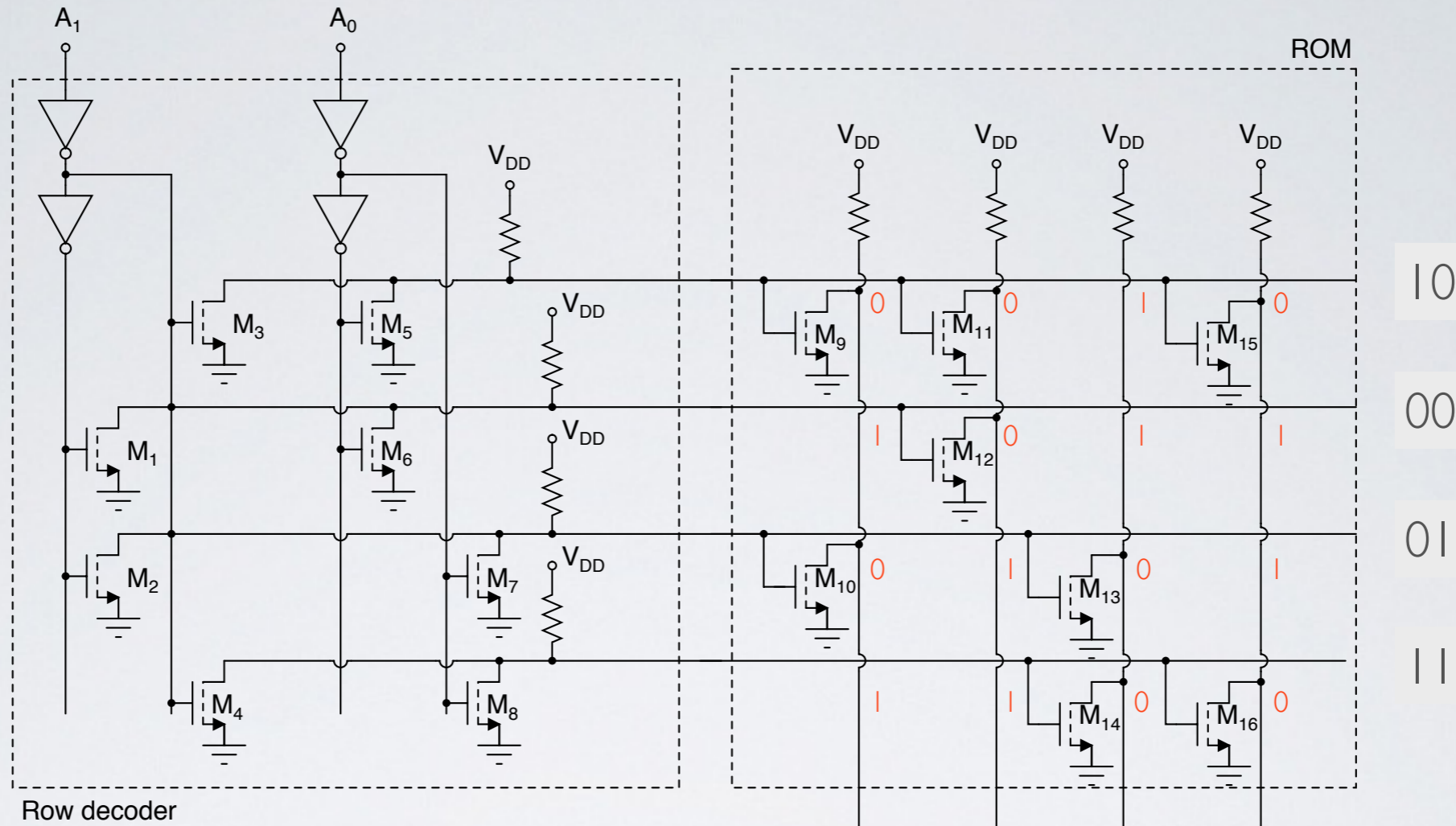


address $A_3A_2A_1A_0$	$D_O$	transistors "ON" (subscripts only)
0101		
1000		
0010		
1010		
0001		

0110  
1100  
0111  
1101  
1011

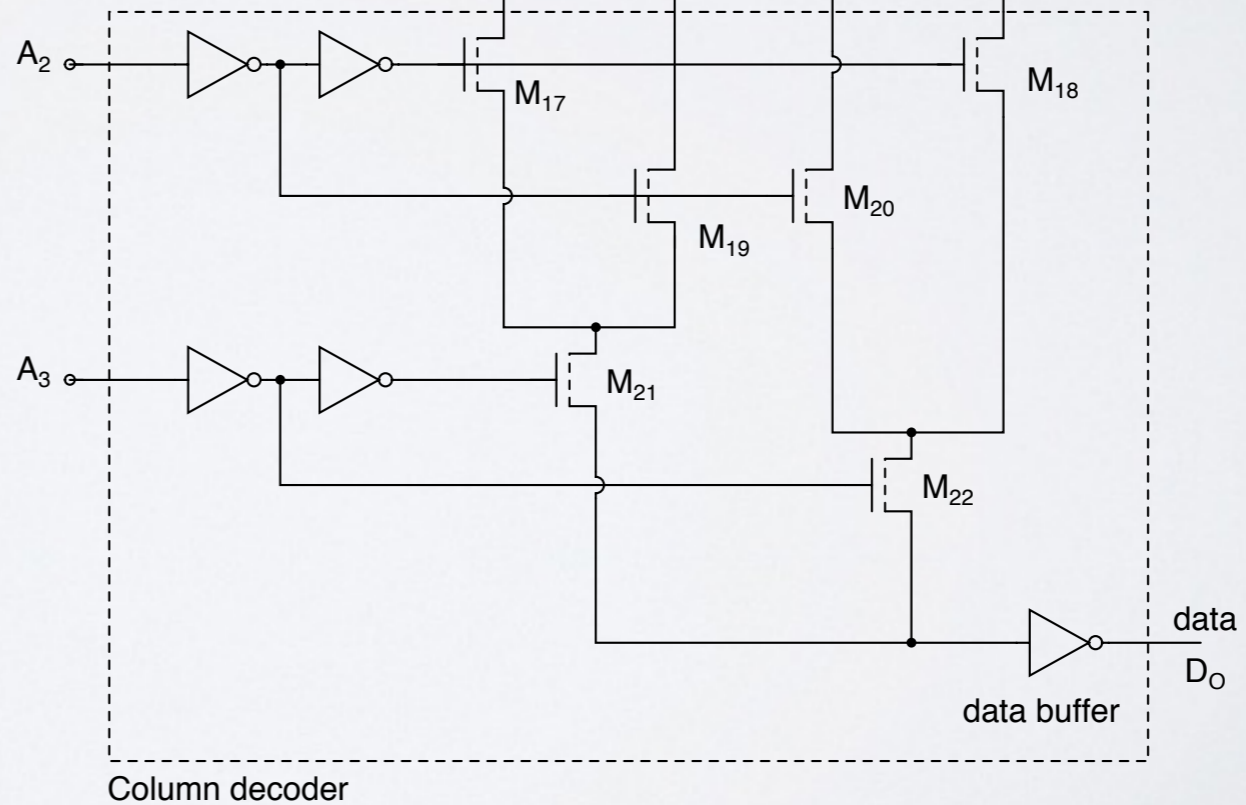


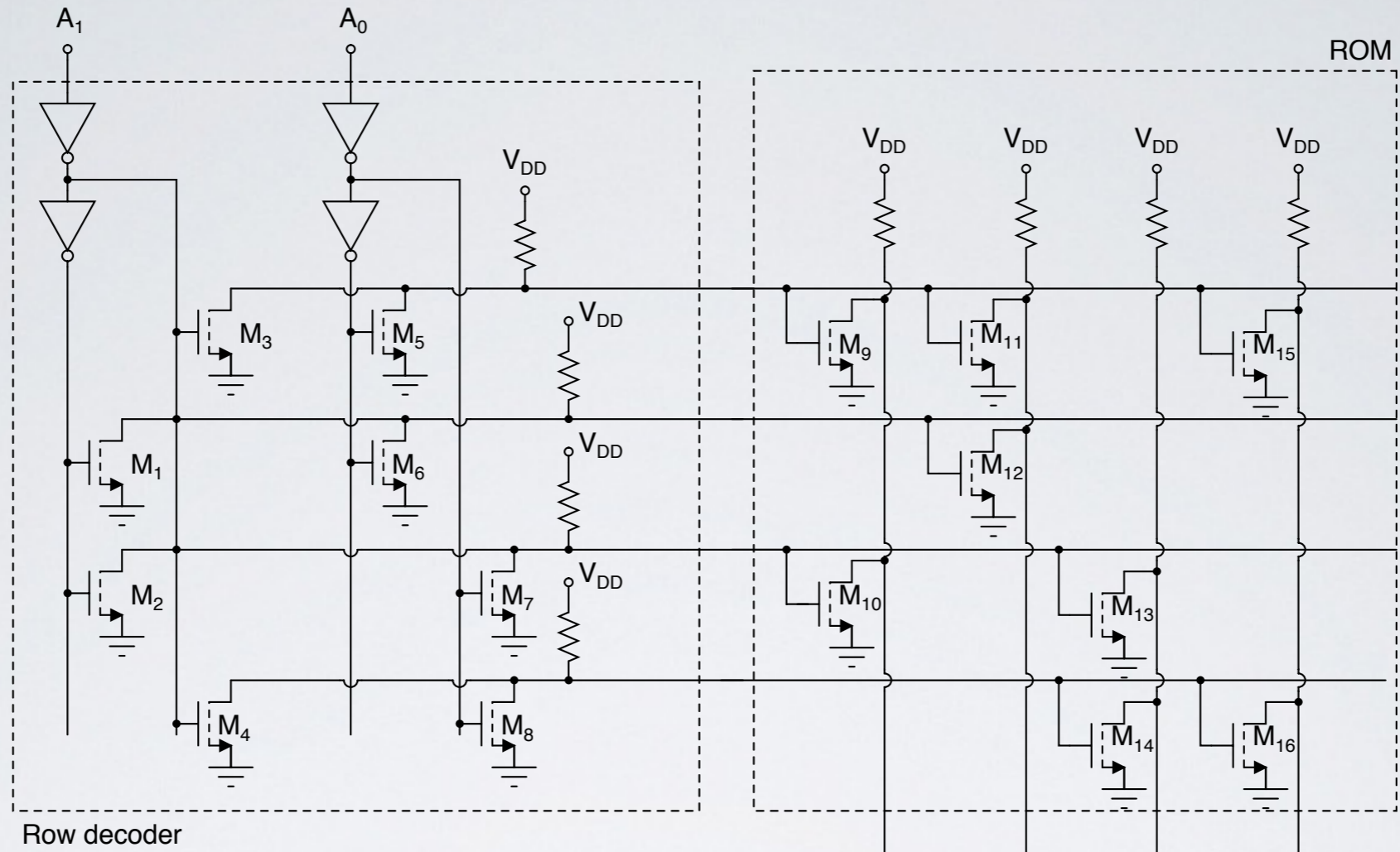




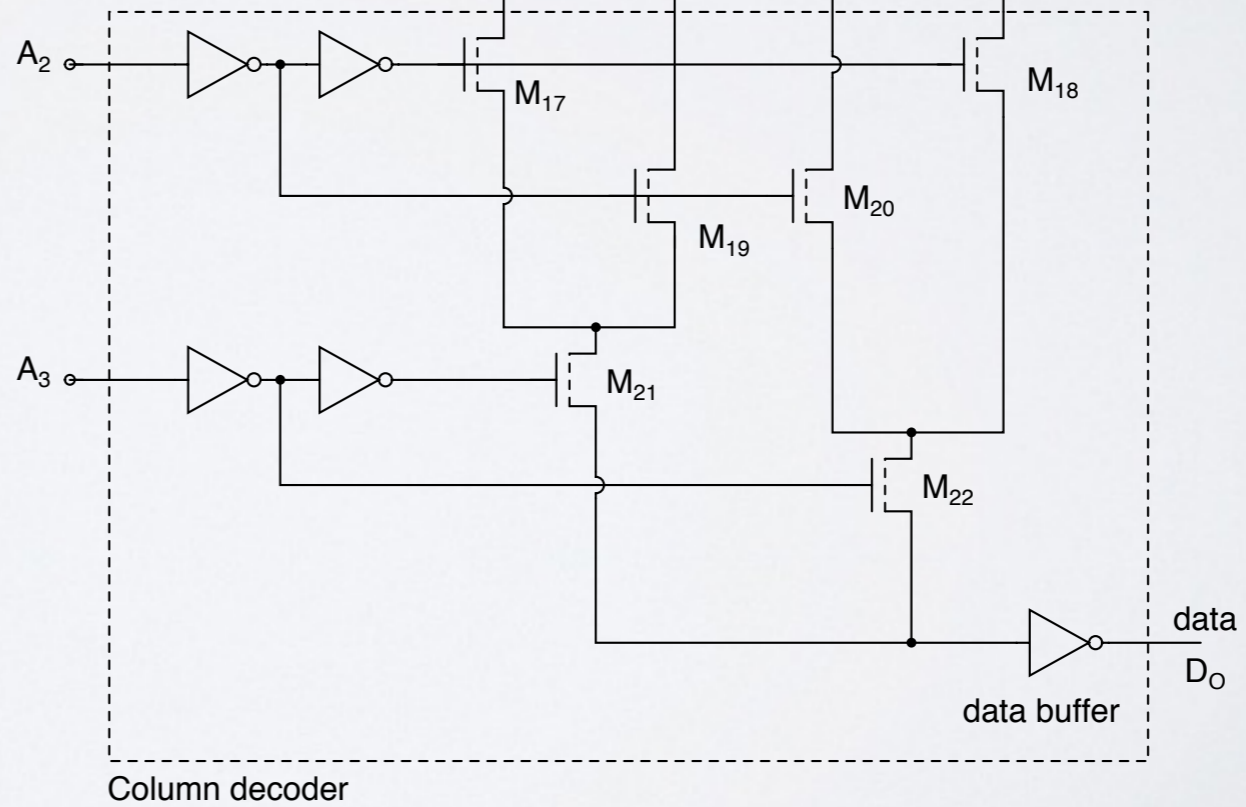
- 0110
- 1100
- 0111
- 1101
- 1011

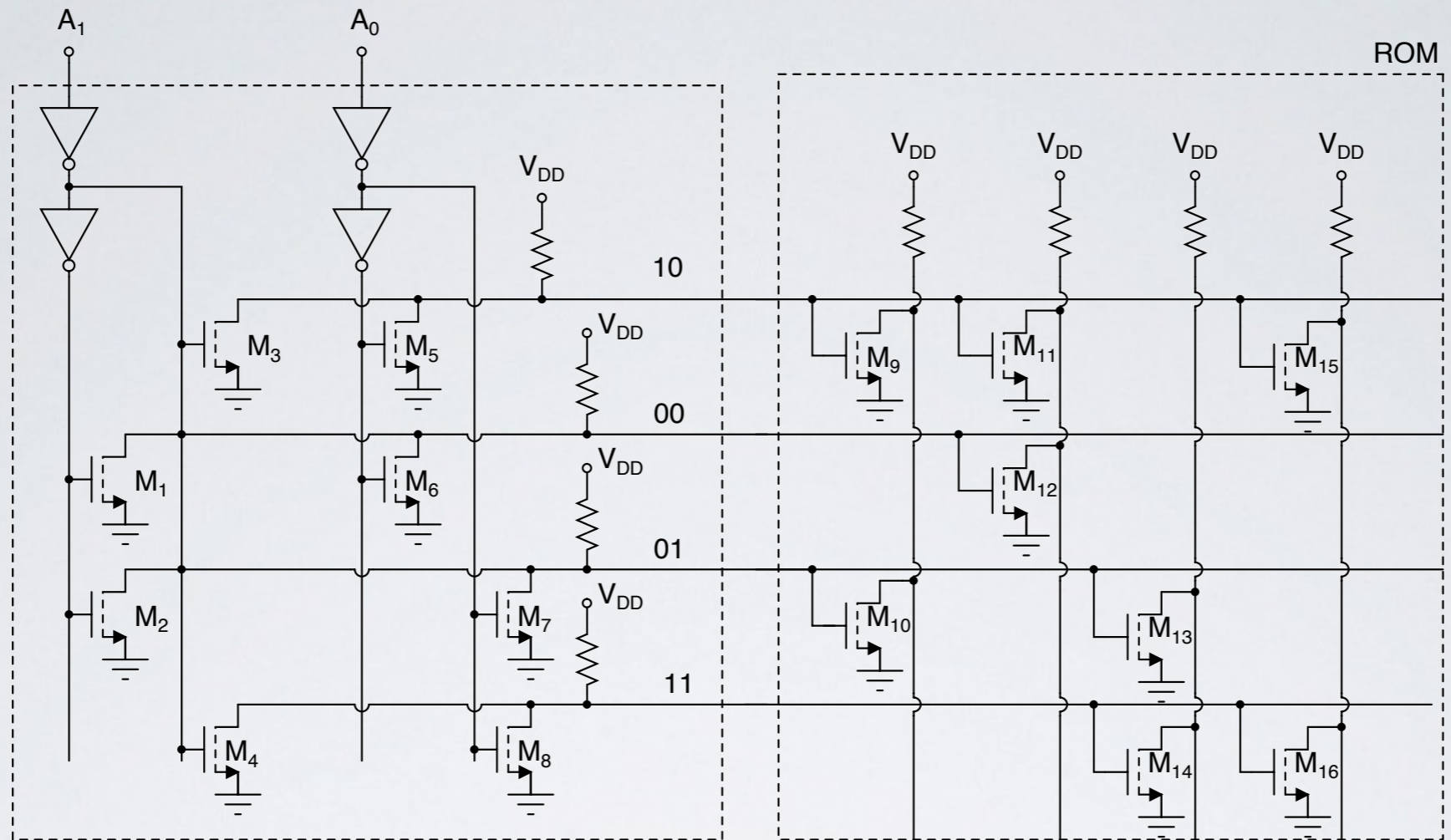
address $A_3A_2A_1A_0$	$D_0$	transistors "ON" (subscripts only)
0101		
1000	0	
0010		
1010		
0001	0	





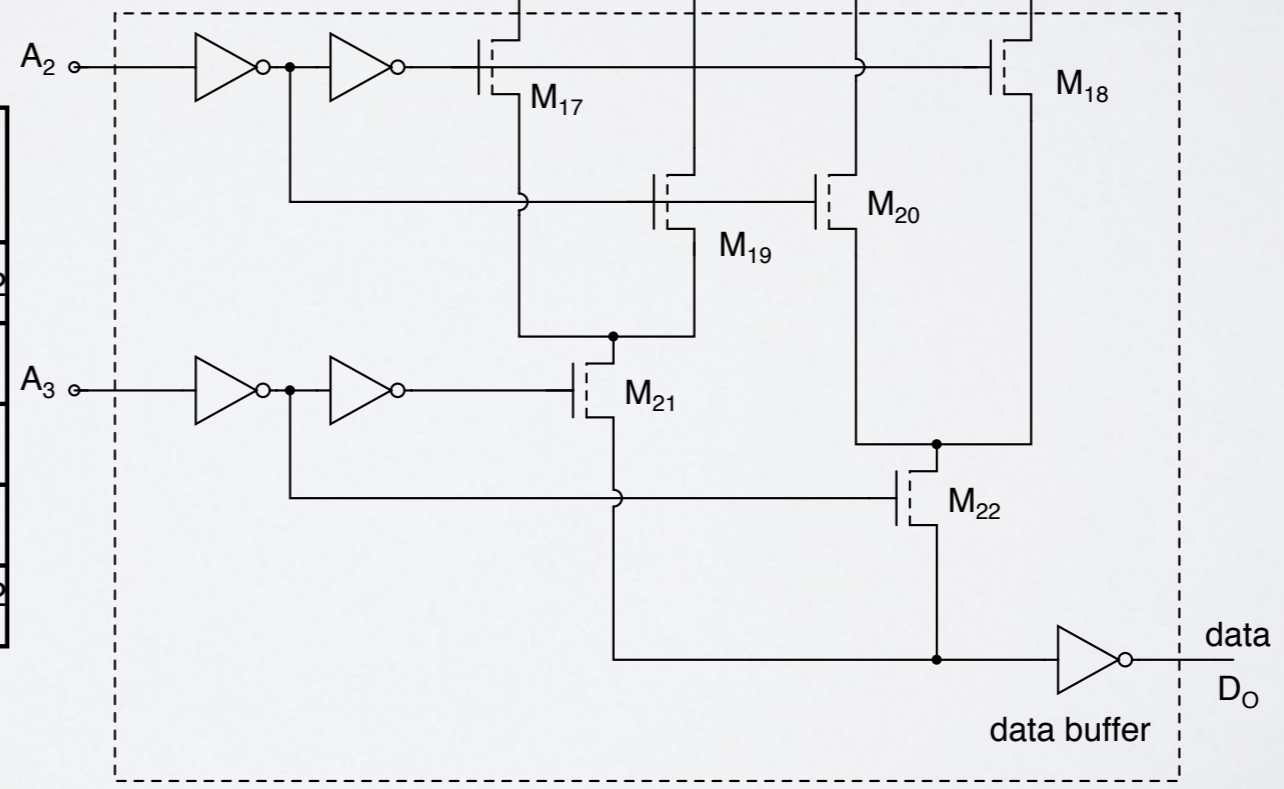
address $A_3A_2A_1A_0$	$D_0$	transistors "ON" (subscripts only)
0101		
1000		
0010		
1010		
0001		





Row decoder

address $A_3A_2A_1A_0$	$D_0$	transistors "ON" (subscripts only)
0101	0	3,4,5,6,10,13,17,18,22
1000	1	3,4,7,8,12,19,20,21
0010	0	1,2,7,8,9,11,15,19,20,22
1010	1	1,2,7,8,9,11,15,19,20,21
0001	1	3,4,5,6,10,13,19,20,22



Column decoder

ROM

data  
 $D_0$

data buffer